

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	659	(327/205).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	IS&R	L2	325	(327/206).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	150	2 not 1	US-PGPUB; USPAT
4	IS&R	L7	731	(327/112).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L8	193	hysteresis.clm. and transistor\$1.clm.	US-PGPUB
6	BRS	L9	173	8 and first.clm.	US-PGPUB
7	BRS	L10	173	9 and second.clm.	US-PGPUB
8	BRS	L11	99	10 and gate\$1.clm.	US-PGPUB
9	BRS	L12	68	11 and input.clm.	US-PGPUB
10	BRS	L13	67	12 and output.clm.	US-PGPUB